

# NCP3064, NCP3064B, NCV3064



ON Semiconductor®

<http://onsemi.com>

## Inverting Converter, Switching Regulator - Buck Boost, ON/OFF Function

### 1.5 A

The NCP3064 Series is a higher frequency upgrade to the popular MC33063A and MC34063A monolithic DC-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step-Down and Step-Up and Voltage-Inverting applications with a minimum number of external components. The ON/OFF pin provides a low power shutdown mode.

#### Features

- Input Voltage Range from 3.0 V to 40 V
- Logic Level Shutdown Capability
- Low Power Standby Mode, Typical 100  $\mu$ A
- Output Switch Current to 1.5 A
- Adjustable Output Voltage Range
- 150 kHz Frequency Operation
- Precision 1.5% Reference
- Internal Thermal Shutdown Protection
- Cycle-by-Cycle Current Limiting
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- These are Pb-Free Devices

#### Applications

- Step-Down, Step-Up and Inverting supply applications
- High Power LED Lighting
- Battery Chargers

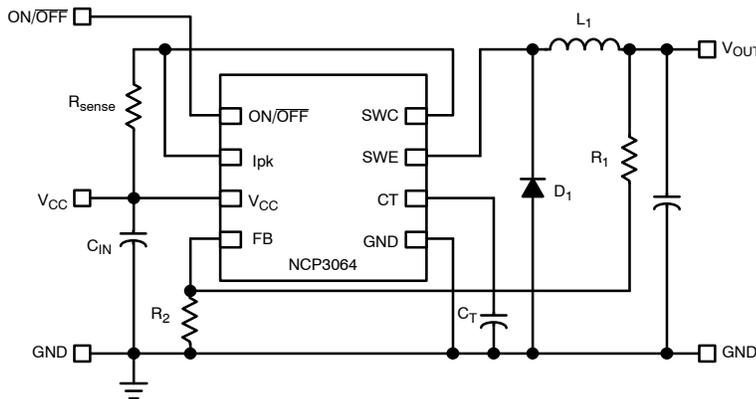
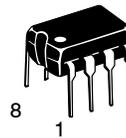
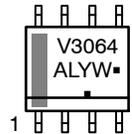
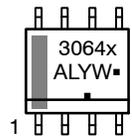


Figure 1. Typical Buck Application Circuit

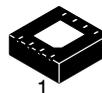
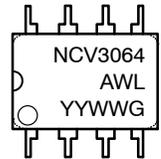
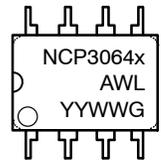
#### MARKING DIAGRAMS



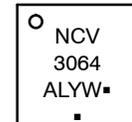
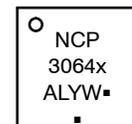
SOIC-8  
D SUFFIX  
CASE 751



PDIP-8  
P, P1 SUFFIX  
CASE 626



DFN8  
MN SUFFIX  
CASE 488AF



NCP3064 = Specific Device Code  
x = B  
A = Assembly Location  
L, WL = Wafer Lot  
Y, YY = Year  
W, WW = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 17 of this data sheet.

# NCP3064, NCP3064B, NCV3064

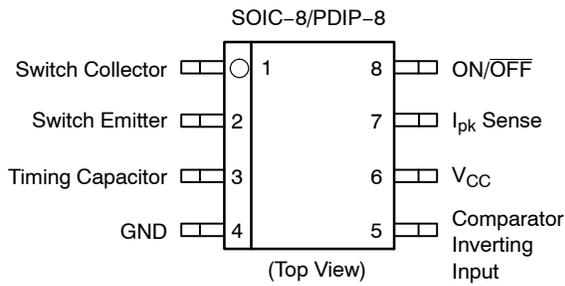
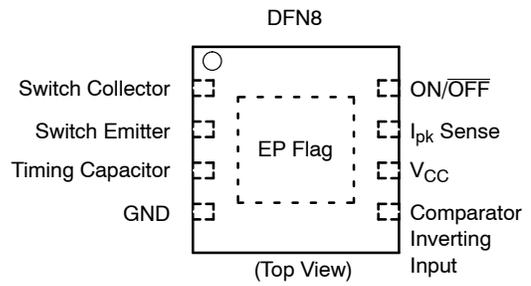


Figure 2. Pin Connections



NOTE: EP Flag must be tied to GND Pin 4 on PCB

Figure 3. Pin Connections

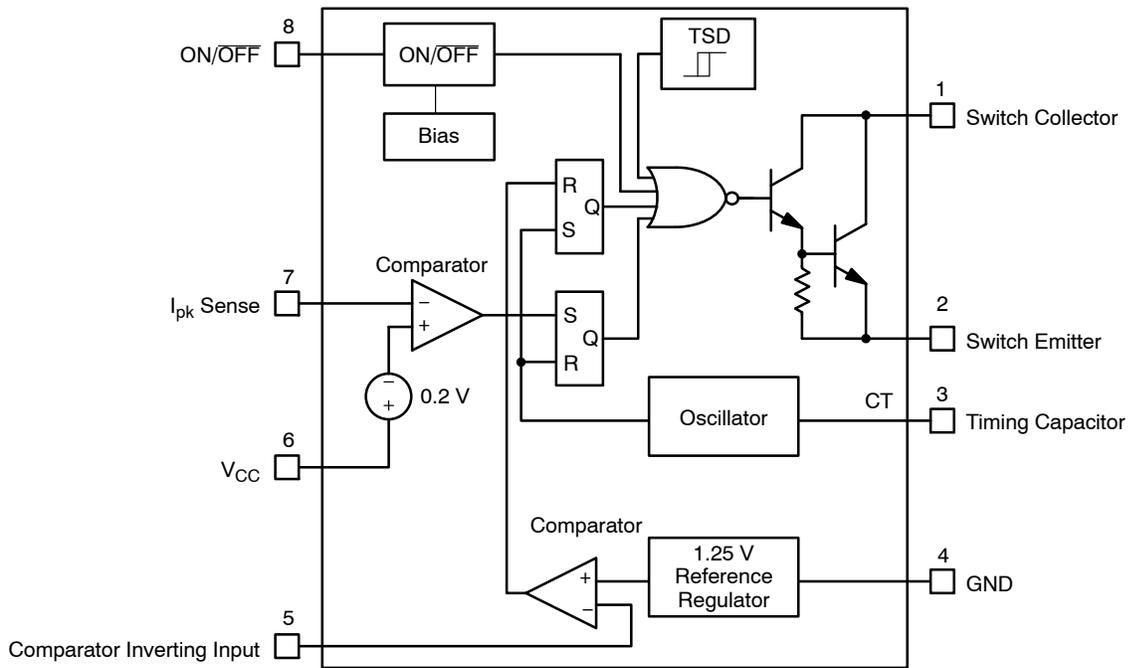


Figure 4. Block Diagram

## PIN DESCRIPTION

| Pin No. | Pin Name                   | Description   |
|---------|----------------------------|---|
| 1       | Switch Collector           | Internal Darlington switch collector  |
| 2       | Switch Emitter             | Internal Darlington switch emitter  |
| 3       | Timing Capacitor           | Timing Capacitor Oscillator Input, Timing Capacitor   |
| 4       | GND                        | Ground pin for all internal circuits  |
| 5       | Comparator Inverting Input | Inverting input pin of internal comparator  |
| 6       | V <sub>CC</sub>            | Voltage supply  |
| 7       | I <sub>pk</sub> Sense      | Peak Current Sense Input to monitor the voltage drop across an external resistor to limit the peak current through the circuit  |
| 8       | ON/OFF                     | ON/OFF Pin. Pulling this pin to High level turns the device in Operating. To switch into mode with low current consumption this pin has to be in Low level or floating. |

# NCP3064, NCP3064B, NCV3064

## MAXIMUM RATINGS (measured vs. Pin 4, unless otherwise noted)

| RATING   | SYMBOL              | VALUE                             | UNIT |
|--|---------------------|-----------------------------------|------|
| V <sub>CC</sub> (Pin 6)  | V <sub>CC</sub>     | -0.3 to 42                        | V    |
| Comparator Inverting Input (Pin 5)                                       | V <sub>CI</sub>     | -0.3 to V <sub>CC</sub>           | V    |
| Darlington Switch Emitter (Pin 2) (Transistor OFF)                       | V <sub>SWE</sub>    | -0.6 to V <sub>CC</sub>           | V    |
| Darlington Switch Collector (Pin 1)                                      | V <sub>SWC</sub>    | -0.3 to 42                        | V    |
| Darlington Switch Collector to Emitter (Pins 1 and 2)                    | V <sub>SWCE</sub>   | -0.3 to 42                        | V    |
| Darlington Switch Peak Current   | I <sub>SW</sub>     | 1.5                               | A    |
| I <sub>pk</sub> Sense Voltage (Pin 7)                                    | V <sub>IPK</sub>    | -0.3 to (V <sub>CC</sub> + 0.3 V) | V    |
| Timing Capacitor Pin Voltage (Pin 3)                                     | V <sub>TC</sub>     | -0.2 to +1.4                      | V    |
| Moisture Sensitivity Level   | MSL                 | 1                                 |      |
| Lead Temperature Soldering<br>Reflow (SMD Styles Only), Pb-Free Versions | T <sub>SLD</sub>    | 260                               | °C   |
| ON/OFF Pin Voltage   | V <sub>ON/OFF</sub> | (-0.3 to 25) < V <sub>CC</sub>    | V    |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTIC

| Rating  | Symbol             | Value                   | Unit |
|---|--------------------|-------------------------|------|
| PDIP-8 (Note 5) Thermal Resistance Junction-to-Air                            | R <sub>θJA</sub>   | 100                     | °C/W |
| SOIC-8 (Note 5) Thermal Resistance Junction-to-Air                            | R <sub>θJA</sub>   | 180                     | °C/W |
| SOIC-8 (Note 5) Thermal Resistance Junction-to-Case                           | R <sub>θJC</sub>   | 45                      | °C/W |
| DFN-8 (Note 5) Thermal Resistance Junction-to-Air                             | R <sub>θJA</sub>   | 78                      | °C/W |
| DFN-8 (Note 5) Thermal Resistance Junction-to-Case                            | R <sub>θJC</sub>   | 14                      | °C/W |
| Storage temperature range   | T <sub>STG</sub>   | -65 to +150             | °C   |
| Maximum junction temperature  | T <sub>J MAX</sub> | +150                    | °C   |
| Operation Junction Temperature Range (Note 3)<br>NCP3064<br>NCP3064B, NCV3064 | T <sub>J</sub>     | 0 to +70<br>-40 to +125 | °C   |

- This device series contains ESD protection and exceeds the following tests:  
Pins 1 through 8:  
Human Body Model 2000 V per AEC Q100-002; 003 or JESD22/A114; A115  
Machine Model Method 200 V
- This device contains latch-up protection and exceeds 100 mA per JEDEC Standard JESD78.
- The relation between junction temperature, ambient temperature and Total Power dissipated in IC is  $T_J = T_A + R_{\theta} \cdot P_D$ .
- The pins which are not defined may not be loaded by external signals.
- 1 oz copper, 1 in<sup>2</sup> copper area.

# NCP3064, NCP3064B, NCV3064

**ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 5.0\text{ V}$ ,  $-40^{\circ}\text{C} < T_J < +125^{\circ}\text{C}$  for NCP3064B and NCV3064,  $0^{\circ}\text{C} < T_J < +70^{\circ}\text{C}$  for NCP3064 unless otherwise specified)

| Symbol | Characteristic | Conditions | Min | Typ | Max | Unit |
|--------|----------------|------------|-----|-----|-----|------|
|--------|----------------|------------|-----|-----|-----|------|

## OSCILLATOR

|                        |                                   |  |     |      |     |               |
|------------------------|-----------------------------------|--|-----|------|-----|---------------|
| $f_{OSC}$              | Frequency                         | ( $V_{Pin\ 5} = 0\text{ V}$ , $C_T = 2.2\text{ nF}$ , $T_J = 25^{\circ}\text{C}$ ) | 110 | 150  | 190 | kHz           |
| $I_{DISCHG} / I_{CHG}$ | Discharge to Charge Current Ratio | (Pin 7 to $V_{CC}$ , $T_J = 25^{\circ}\text{C}$ )                                  | 5.5 | 6.0  | 6.5 | –             |
| $I_C$                  | Capacitor Charging Current        | (Pin 7 to $V_{CC}$ , $T_J = 25^{\circ}\text{C}$ )                                  |     | 275  |     | $\mu\text{A}$ |
| $I_{DISCH}$            | Capacitor Discharging Current     | (Pin 7 to $V_{CC}$ , $T_J = 25^{\circ}\text{C}$ )                                  |     | 1.65 |     | mA            |
| $V_{IPK}$              | Current Limit Sense Voltage       | ( $T_J = 25^{\circ}\text{C}$ )   | 165 | 200  | 235 | mV            |

## OUTPUT SWITCH (Note 6)

|              |   |  |  |     |     |               |
|--------------|---|--|--|-----|-----|---------------|
| $V_{SWCE}$   | Darlington Switch Collector to Emitter Voltage Drop | ( $I_{SW} = 1.0\text{ A}$ , $T_J = 25^{\circ}\text{C}$ )<br>(Note 6) |  | 1.0 | 1.3 | V             |
| $I_{C(OFF)}$ | Collector Off-State Current                         | ( $V_{CE} = 40\text{ V}$ )   |  | 1.0 | 10  | $\mu\text{A}$ |

## COMPARATOR

|               |                                   |  |       |      |      |    |
|---------------|-----------------------------------|--|-------|------|------|----|
| $V_{TH}$      | Threshold Voltage                 | $T_J = 25^{\circ}\text{C}$                 |       | 1.25 |      | V  |
|               |                                   | NCP3064                                    | –1.5  |      | +1.5 | %  |
|               |                                   | NCP3064B, NCV3064                          | –1.5  |      | +1.5 | %  |
| $REG_{LINE}$  | Threshold Voltage Line Regulation | ( $V_{CC} = 3.0\text{ V to }40\text{ V}$ ) | –6.0  | 2.0  | 6.0  | mV |
| $I_{CII\ in}$ | Input Bias Current                | ( $V_{in} = V_{th}$ )                      | –1000 | –100 | 1000 | nA |

## ON/OFF FEATURE

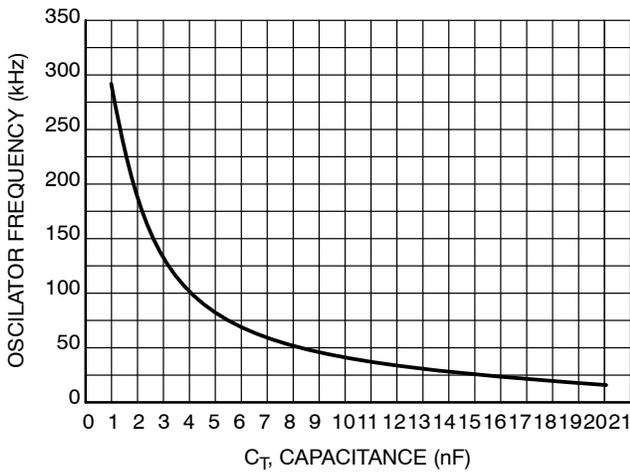
|          |  |   |     |     |     |               |
|----------|--|---|-----|-----|-----|---------------|
| $V_{IH}$ | ON/OFF Pin Logic Input Level High<br>$V_{OUT} = \text{Nominal Output Voltage}$ | $T_J = 25^{\circ}\text{C}$                          | 2.2 | –   | –   | V             |
|          |  | $T_J = -40^{\circ}\text{C to }+125^{\circ}\text{C}$ | 2.4 | –   | –   |               |
| $V_{IL}$ | ON/OFF Pin Logic Input Level Low<br>$V_{OUT} = 0\text{ V}$                     | $T_J = 25^{\circ}\text{C}$                          | –   | –   | 1.0 | V             |
|          |  | $T_J = -40^{\circ}\text{C to }+125^{\circ}\text{C}$ | –   | –   | 0.8 |               |
| $I_{IH}$ | ON/OFF Pin Input Current<br>ON/OFF Pin = 5 V (ON)                              | $T_J = 25^{\circ}\text{C}$                          |     | 15  |     | $\mu\text{A}$ |
| $I_{IL}$ | ON/OFF Pin Input Current<br>ON/OFF Pin = 0 V (OFF)                             | $T_J = 25^{\circ}\text{C}$                          |     | 1.0 |     | $\mu\text{A}$ |

## TOTAL DEVICE

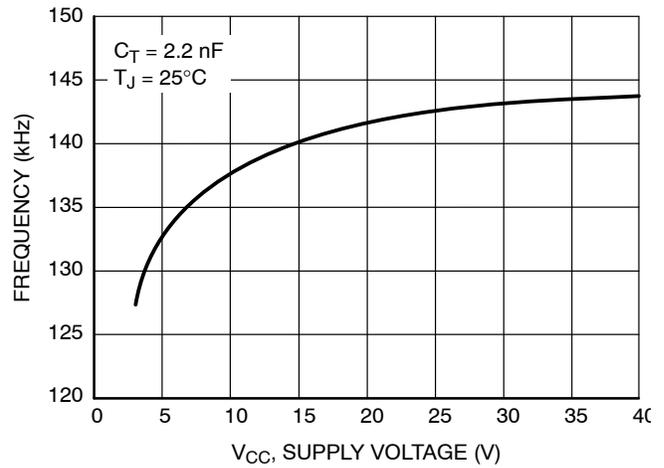
|              |                            |  |  |     |            |                    |
|--------------|----------------------------|--|--|-----|------------|--------------------|
| $I_{CC}$     | Supply Current             | ( $V_{CC} = 5.0\text{ V to }40\text{ V}$ ,<br>$C_T = 2.2\text{ nF}$ , Pin 7 = $V_{CC}$ ,<br>$V_{Pin\ 5} > V_{th}$ , Pin 2 = GND,<br>remaining pins open) |  |     | 7.0        | mA                 |
| $I_{STBY}$   | Standby Quiescent Current  | ON/OFF Pin = 0 V (OFF)<br>$T_J = 25^{\circ}\text{C}$<br>$T_J = -40^{\circ}\text{C to }+125^{\circ}\text{C}$  |  | 85  | 100<br>100 | $\mu\text{A}$      |
| $T_{SHD}$    | Thermal Shutdown Threshold |  |  | 160 |            | $^{\circ}\text{C}$ |
| $T_{SHDHYS}$ | Hysteresis                 |  |  | 10  |            | $^{\circ}\text{C}$ |

- Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.
- The  $V_{IPK}$  (Sense) Current Limit Sense Voltage is specified at static conditions. In dynamic operation the sensed current turn-off value depends on comparator response time and di/dt current slope. See the Operating Description section for details.

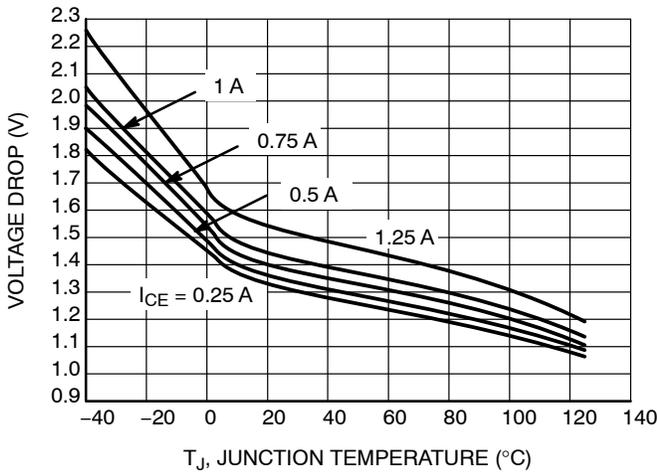
# NCP3064, NCP3064B, NCV3064



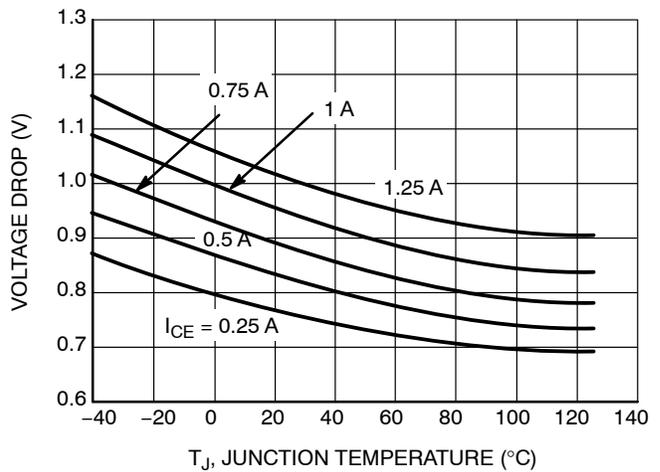
**Figure 5. Oscillator Frequency vs. Timing Capacitor  $C_T$**



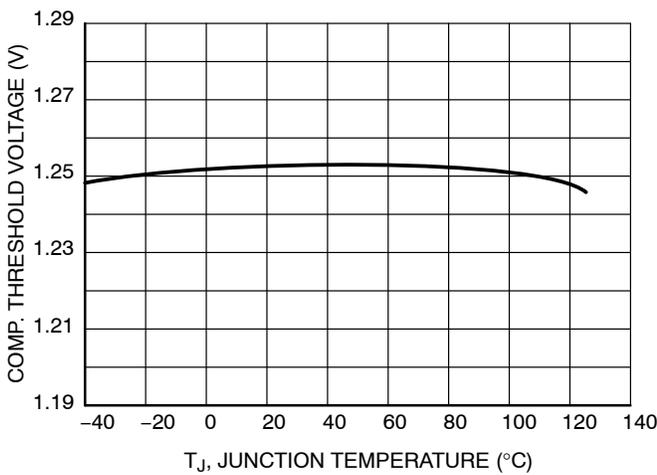
**Figure 6. Oscillator Frequency vs. Supply Voltage**



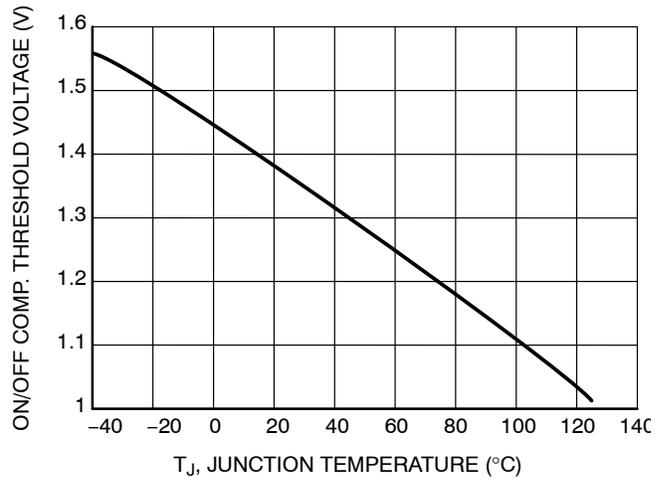
**Figure 7. Emitter Follower Configuration Output Darlington Switch Voltage Drop vs. Temperature**



**Figure 8. Common Emitter Configuration Output Darlington Switch Voltage Drop vs. Temperature**

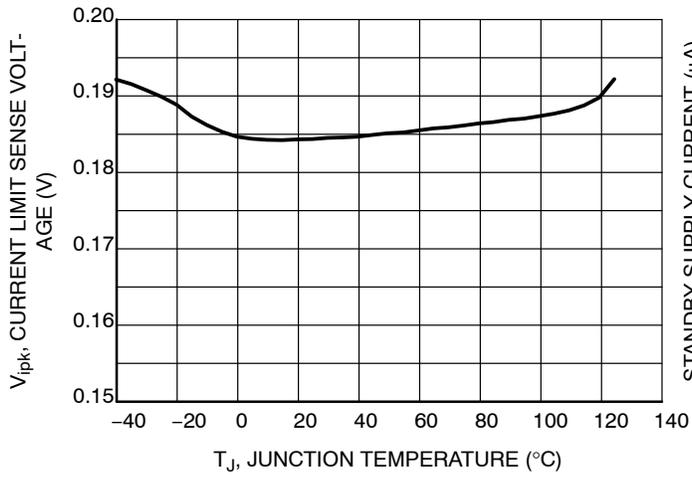


**Figure 9. Comparator Threshold Voltage vs. Temperature**

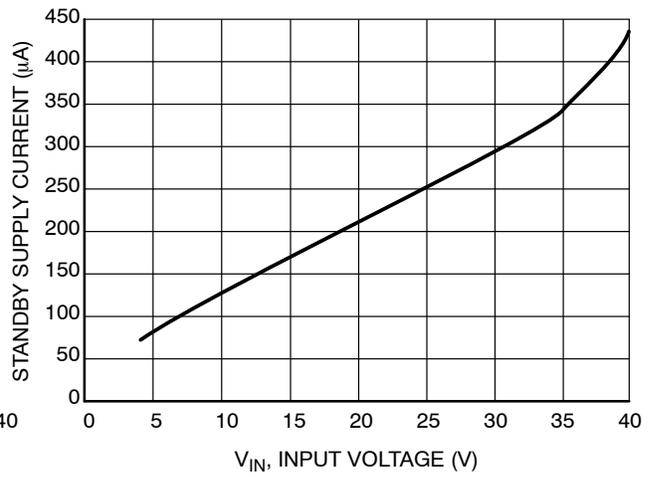


**Figure 10. ON/OFF Comparator Threshold Voltage vs. Temperature**

# NCP3064, NCP3064B, NCV3064



**Figure 11. Current Limit Sense Voltage vs. Temperature**



**Figure 12. Standby Current vs. Supply Voltage**

INTRODUCTION

The NCP3064 is a monolithic power switching regulator optimized for dc to dc converter applications. The combination of its features enables the system designer to directly implement step-up, step-down, and voltage-inverting converters with a minimum number of external components. Potential applications include cost sensitive consumer products as well as equipment for industrial markets. A representative block diagram is shown in Figure 4.

Operating Description

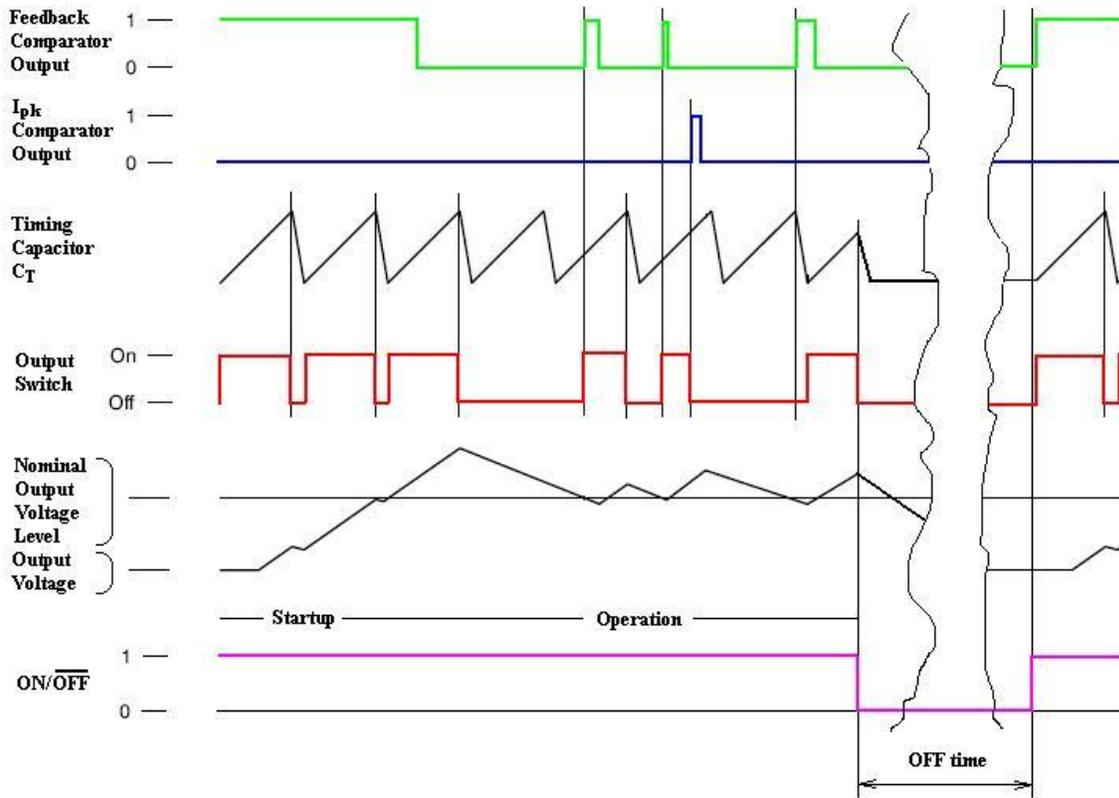
The NCP3064 is a hysteric, dc-dc converter that uses a gated oscillator to regulate output voltage. In general, this mode of operation is some what analogous to a capacitor charge pump and does not require dominant pole loop compensation for converter stability. The Typical Operating Waveforms are shown in Figure 13. The output voltage waveform shown is for a step-down converter with the ripple and phasing exaggerated for clarity. During initial converter startup, the feedback comparator senses that the output voltage level is below nominal. This causes the output switch to turn on and off at a frequency and duty cycle controlled by the oscillator, thus pumping up the output filter

capacitor. When the output voltage level reaches nominal, the output switch next cycle turning on is inhibited. The feedback comparator will enable the switching immediately when the load current causes the output voltage to fall below nominal. Under these conditions, output switch conduction can be enabled for a partial oscillator cycle, a partial cycle plus a complete cycle, multiple cycles, or a partial cycle plus multiple cycles.

Oscillator

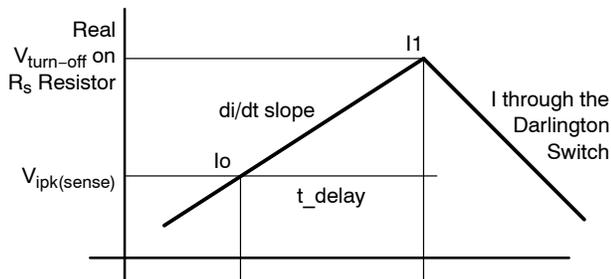
The oscillator frequency and off-time of the output switch are programmed by the value selected for the timing capacitor  $C_T$ . Capacitor  $C_T$  is charged and discharged by a 1 to 6 ratio internal current source and sink, generating a positive going sawtooth waveform at Pin 3. This ratio sets the maximum  $t_{ON}/(t_{ON} + t_{OFF})$  of the switching converter as  $6/(6 + 1)$  or 0.857 (typical).

The oscillator peak and valley voltage difference is 500 mV typically. To calculate the  $C_T$  capacitor value for the required oscillator frequency, use the equation found in Figure 15. An Excel® based design tool can be found at [www.onsemi.com](http://www.onsemi.com) on the NCP3064 product page.



**Peak Current Sense Comparator**

With a voltage ripple gated converter operating under normal conditions, output switch conduction is initiated by the Voltage Feedback comparator and terminated by the oscillator. Abnormal operating conditions occur when the converter output is overloaded or when feedback voltage sensing is lost. Under these conditions, the I<sub>pk</sub> Current Sense comparator will protect the Darlington output Switch. The switch current is converted to a voltage by inserting a fractional Ω resistor, R<sub>SC</sub>, in series with V<sub>CC</sub> and the Darlington output switch. The voltage drop across R<sub>SC</sub> is monitored by the Current Sense comparator. If the voltage drop exceeds 200 mV with respect to V<sub>CC</sub>, the comparator will set the latch and terminate output switch conduction on a cycle-by-cycle basis. This Comparator/Latch configuration ensures that the Output Switch has only a single on-time during a given oscillator cycle.



**Figure 14. Current Sense Waveform**

The V<sub>IPK(Sense)</sub> Current Limit Sense Voltage threshold is specified at static conditions. In dynamic operation the sensed current turn-off value depends on comparator response time and di/dt current slope.

Real V<sub>turn-off</sub> on R<sub>SC</sub> resistor

$$V_{turn-off} = V_{ipk(sense)} + R_S * (t_{delay} * di/dt)$$

Typical I<sub>pk</sub> comparator response time t<sub>delay</sub> is 350 ns. The di/dt current slope is growing with voltage difference on the

inductor pins and with decreasing inductor value. It is recommended to check the real max peak current in the application at worst conditions to be sure that the maximum peak current will never get over the 1.5 A Darlington Switch Current maximum rating.

**Thermal Shutdown**

Internal thermal shutdown circuitry is provided to protect the IC in the event that the maximum junction temperature is exceeded. When activated, typically at 160°C, the Output Switch is disabled. The temperature sensing circuit is designed with 10°C hysteresis. The Switch is enabled again when the chip temperature decreases to at least 150°C threshold. This feature is provided to prevent catastrophic failures from accidental device overheating. It is not intended to be used as a replacement for proper heat-sinking.

**Output Switch**

The output switch is designed in a Darlington configuration. This allows the application designer to operate at all conditions at high switching speed and low voltage drop. The Darlington Output Switch is designed to switch a maximum of 40 V collector to emitter voltage and current up to 1.5 A

**ON/OFF Function**

The ON/OFF function disables switching and puts the part into a low power consumption mode. A PWM signal up to 1 kHz can be used to pulse the ON/OFF and control the output. Pulling this pin below the threshold voltage (~1.4 V) or leaving it open turns the regulator off and has a standby current <100 μA. Pulling this pin above 1.4 V (up to 25 V max) allows the regulator to run in normal operation. If the ON/OFF feature is not needed, the ON/OFF pin can be connected to the input voltage V<sub>CC</sub>, provided that this voltage does not exceed 25 V.

APPLICATIONS

Figures 16, 20 and 24 show the simplicity and flexibility of the NCP3064. Two main converter topologies are demonstrated with actual test data shown below the circuit diagrams.

Figure 15 gives the relevant design equations for the key parameters. Additionally, a complete application design aid for the NCP3064 can be found at [www.onsemi.com](http://www.onsemi.com).

It is possible to create applications with external transistors. This solution helps to increase output current and helps with efficiency, still keeping the cost of materials low. Another advantage of using the external transistor is higher operating frequency, which can go up to 250 kHz. Smaller size of the output components such as inductor and capacitor can be used then.

| (See Notes 8, 9, 10)      | Step-Down   | Step-Up   | Voltage-Inverting   |
|---------------------------|---|---|---|
| $\frac{t_{on}}{t_{off}}$  | $\frac{V_{out} + V_F}{V_{in} - V_{SWCE} - V_{out}}$                       | $\frac{V_{out} + V_F - V_{in}}{V_{in} - V_{SWCE}}$                        | $\frac{ V_{out}  + V_F}{V_{in} - V_{SWCE}}$                               |
| $t_{on}$                  | $\frac{t_{on}}{t_{off}}$<br>$f \left( \frac{t_{on}}{t_{off}} + 1 \right)$ | $\frac{t_{on}}{t_{off}}$<br>$f \left( \frac{t_{on}}{t_{off}} + 1 \right)$ | $\frac{t_{on}}{t_{off}}$<br>$f \left( \frac{t_{on}}{t_{off}} + 1 \right)$ |
| $C_T$                     | $C_T = \frac{381.6 \cdot 10^{-6}}{f_{osc}} - 343 \cdot 10^{-12}$          |   |   |
| $I_{L(avg)}$              | $I_{out}$   | $I_{out} \left( \frac{t_{on}}{t_{off}} + 1 \right)$                       | $I_{out} \left( \frac{t_{on}}{t_{off}} + 1 \right)$                       |
| $I_{pk} \text{ (Switch)}$ | $I_{L(avg)} + \frac{\Delta I_L}{2}$                                       | $I_{L(avg)} + \frac{\Delta I_L}{2}$                                       | $I_{L(avg)} + \frac{\Delta I_L}{2}$                                       |
| $R_{SC}$                  | $\frac{0.20}{I_{pk} \text{ (Switch)}}$                                    | $\frac{0.20}{I_{pk} \text{ (Switch)}}$                                    | $\frac{0.20}{I_{pk} \text{ (Switch)}}$                                    |
| $L$                       | $\left( \frac{V_{in} - V_{SWCE} - V_{out}}{\Delta I_L} \right) t_{on}$    | $\left( \frac{V_{in} - V_{SWCE}}{\Delta I_L} \right) t_{on}$              | $\left( \frac{V_{in} - V_{SWCE}}{\Delta I_L} \right) t_{on}$              |
| $V_{ripple(pp)}$          | $\Delta I_L \sqrt{\left( \frac{1}{8 f C_O} \right)^2 + (ESR)^2}$          | $\approx \frac{t_{on} I_{out}}{C_O} + \Delta I_L \cdot ESR$               | $\approx \frac{t_{on} I_{out}}{C_O} + \Delta I_L \cdot ESR$               |
| $V_{out}$                 | $V_{TH} \left( \frac{R_1}{R_2} + 1 \right)$                               | $V_{TH} \left( \frac{R_1}{R_2} + 1 \right)$                               | $V_{TH} \left( \frac{R_1}{R_2} + 1 \right)$                               |

- 8.  $V_{SWCE}$  – Darlington Switch Collector to Emitter Voltage Drop, refer to Figures 7, 5, 8 and 9.
- 9.  $V_F$  – Output rectifier forward voltage drop. Typical value for 1N5819 Schottky barrier rectifier is 0.4 V.
- 10. The calculated  $t_{on}/t_{off}$  must not exceed the minimum guaranteed oscillator charge to discharge ratio.

Figure 15. Design Equations

The Following Converter Characteristics Must Be Chosen:

$V_{in}$  – Nominal operating input voltage.

$V_{out}$  – Desired output voltage.

$I_{out}$  – Desired output current.

$\Delta I_L$  – Desired peak-to-peak inductor ripple current. For maximum output current it is suggested that  $\Delta I_L$  be chosen to be less than 10% of the average inductor current  $I_{L(avg)}$ . This will help prevent  $I_{pk(Switch)}$  from reaching the current limit threshold set by  $R_{SC}$ . If the design goal is to use a minimum inductance value, let  $\Delta I_L = 2(I_{L(avg)})$ . This will proportionally reduce converter output current capability.

$f$  – Maximum output switch frequency.

$V_{ripple(pp)}$  – Desired peak-to-peak output ripple voltage. For best performance the ripple voltage should be kept to a low value since it will directly affect line and load regulation. Capacitor  $C_O$  should be a low equivalent series resistance (ESR) electrolytic designed for switching regulator applications.

# NCP3064, NCP3064B, NCV3064

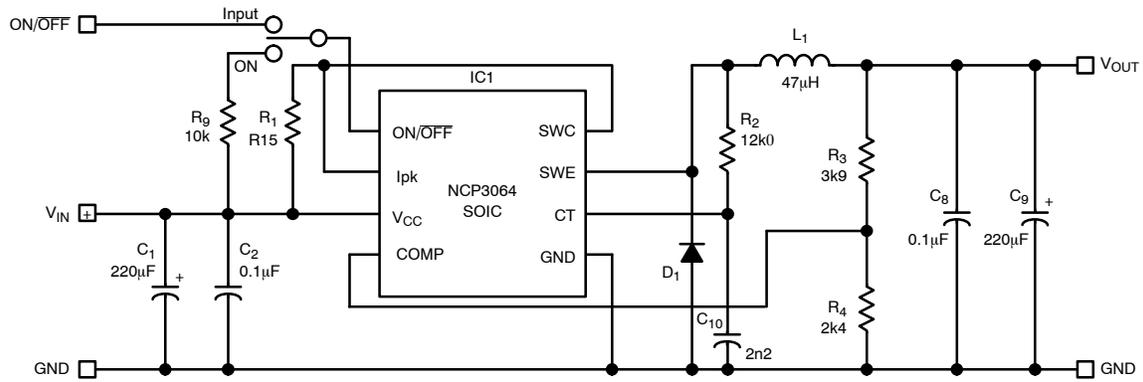


Figure 16. Typical Buck Application Schematic

Table 1. TESTED PARAMETERS

| Parameter | Input Voltage (V) | Output Voltage (V) | Input Current (A) | Output Current (A) |
|-----------|-------------------|--------------------|-------------------|--------------------|
| Value     | 10 – 16           | 3.3                | Max. 0.6 A        | Max. 1.25          |

Table 2. BILL OF MATERIAL

| Designator | Qty | Description         | Value     | Tolerance | Footprint | Manufacturer     | Manufacturer Part Number |
|------------|-----|---------------------|-----------|-----------|-----------|------------------|--------------------------|
| R1         | 1   | Resistor            | 0.15Ω     | 1%        | 1206      | Susumu           | RL1632R-R150-F           |
| R2         | 1   | Resistor            | 12k       | 1%        | 1206      | ROHM             | MCR18EZHf1202            |
| R3         | 1   | Resistor            | 3k9       | 1%        | 1206      | ROHM             | MCR18EZHf3901            |
| R4         | 1   | Resistor            | 2k4       | 1%        | 1206      | ROHM             | MCR18EZHf4701            |
| R9         | 1   | Resistor            | 10k       | 1%        | 1206      | ROHM             | MCR18EZHf1002            |
| C1         | 1   | Capacitor           | 220µF/35V | 20%       | F         | PANASONIC        | EEEF1V221AP              |
| C2, C8     | 2   | Capacitor           | 100nF     | 10%       | 1206      | Kemet            | C1206C104K5RACTU         |
| C9         | 1   | Capacitor           | 220µF/6V  | 20%       | F8        | SANYO            | 6SVP220M                 |
| C10        | 1   | Capacitor           | 2.2nF     | 10%       | 1206      | Kemet            | C1206C222K5RACTU         |
| L1         | 1   | Inductor            | 47µH      | 20%       | DO3316    | CoilCraft        | DO3316P-473MLB           |
| D1         | 1   | Diode               | MBRS230   | -         | SMB       | ON Semiconductor | MBRS230LT3G              |
| IC         | 1   | Switching Regulator | NCP3064   | -         | SOIC8     | ON Semiconductor | NCP3064DR2G              |

# NCP3064, NCP3064B, NCV3064

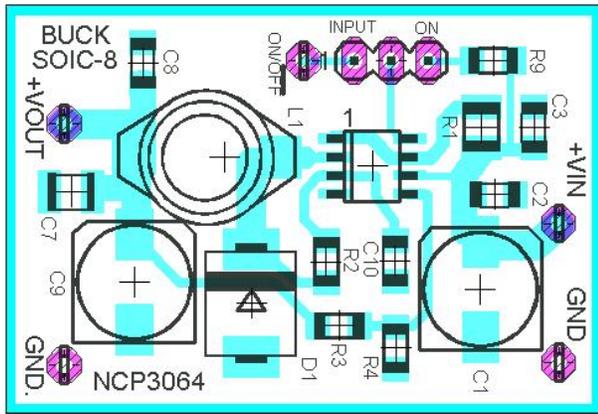


Figure 17. Buck Demoboard Layout

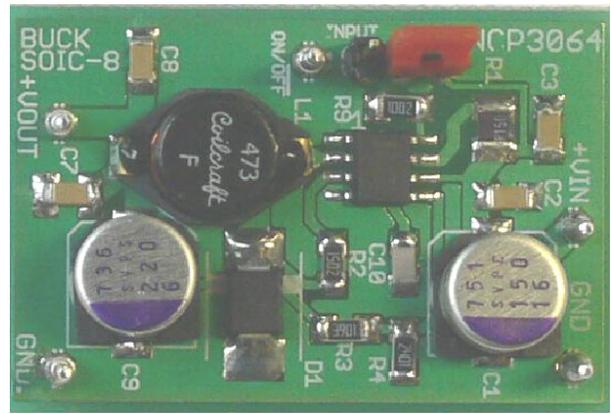


Figure 18. Buck Demoboard Photo

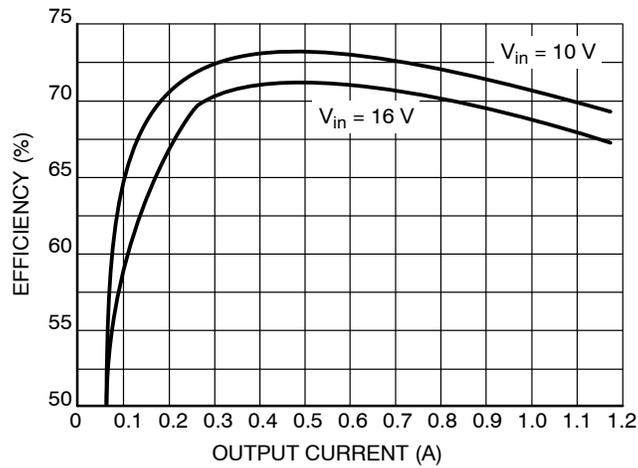


Figure 19. Efficiency vs. Output Current for Buck Demoboard

Table 3. TEST RESULTS

|                 |  |                     |
|-----------------|--|---------------------|
| Line Regulation | $V_{in} = 9\text{ V to }12\text{ V}$ , $V_{out} = 3.3\text{ V}$ , $I_{out} = 800\text{ mA}$    | 8 mV                |
| Load Regulation | $V_{in} = 12\text{ V}$ , $V_{out} = 3.3\text{ V}$ , $I_{out} = 800\text{ mA}$                  | 10 mV               |
| Output Ripple   | $V_{in} = 12\text{ V}$ , $V_{out} = 3.3\text{ V}$ , $I_{out} = 100\text{ mA to }800\text{ mA}$ | < 85 mV Peak - Peak |
| Efficiency      | $V_{in} = 12\text{ V}$ , $V_{out} = 3.3\text{ V}$ , $I_{out} = 500\text{ mA}$                  | 70%                 |

# NCP3064, NCP3064B, NCV3064

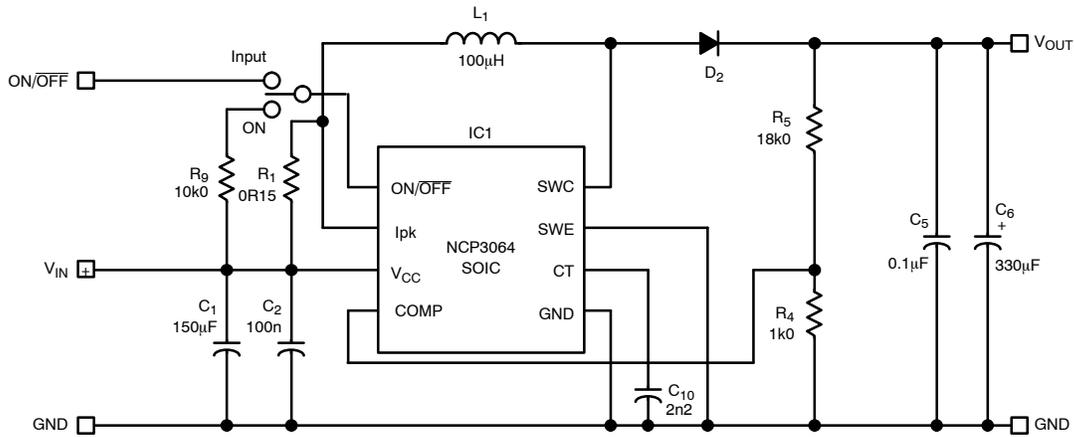


Figure 20. Typical Boost Application Schematic

Table 4. TESTED PARAMETERS

| Parameter | Input Voltage (V) | Output Voltage (V) | Input Current (A) | Output Current (A) |
|-----------|-------------------|--------------------|-------------------|--------------------|
| Value     | 10 – 16           | 24                 | Max. 1.25         | Max. 0.6           |

Table 5. BILL OF MATERIAL

| Designator | Qty | Description         | Value     | Tolerance | Footprint | Manufacturer     | Manufacturer Part Number |
|------------|-----|---------------------|-----------|-----------|-----------|------------------|--------------------------|
| R1         | 1   | Resistor            | 0.15Ω     | 1%        | 1206      | Susumu           | RL1632R-R150-F           |
| R5         | 1   | Resistor            | 18k       | 1%        | 1206      | ROHM             | MCR18EZHF1802            |
| R6         | 1   | Resistor            | 1k        | 1%        | 1206      | ROHM             | MCR18EZHF1001            |
| R9         | 1   | Resistor            | 10k       | 1%        | 1206      | ROHM             | MCR18EZHF1002            |
| C1         | 1   | Capacitor           | 150µF/16V | 20%       | F8        | SANYO            | 6SVP150M                 |
| C2, C5     | 2   | Capacitor           | 100nF     | 10%       | 1206      | Kemet            | C1206C104K5RACTU         |
| C6         | 1   | Capacitor           | 330µF/25V | 20%       | SMD       | Panasonic        | EEE-FK1E331GP            |
| C10        | 1   | Capacitor           | 2.2nF     | 10%       | 1206      | Kemet            | C1206C222K5RACTU         |
| L2         | 1   | Inductor            | 100µH     | 20%       | DO3316    | CoilCraft        | DO3316P-104MLB           |
| D2         | 1   | Diode               | MBRS230   | -         | SMB       | ON Semiconductor | MBRS230LT3G              |
| IC         | 1   | Switching Regulator | NCP3064   | -         | SOIC8     | ON Semiconductor | NCP3064DR2G              |

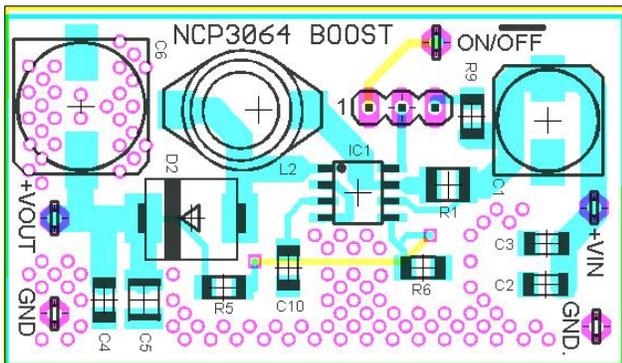


Figure 21. Boost Demoboard Layout

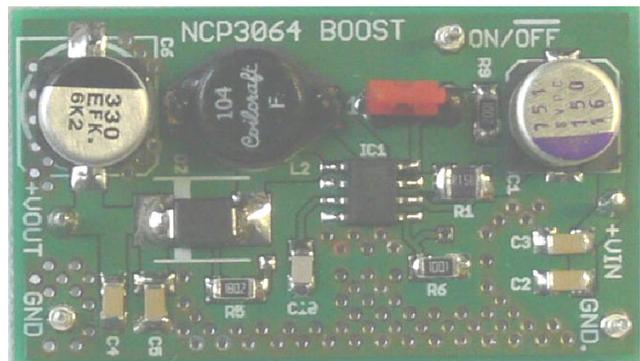
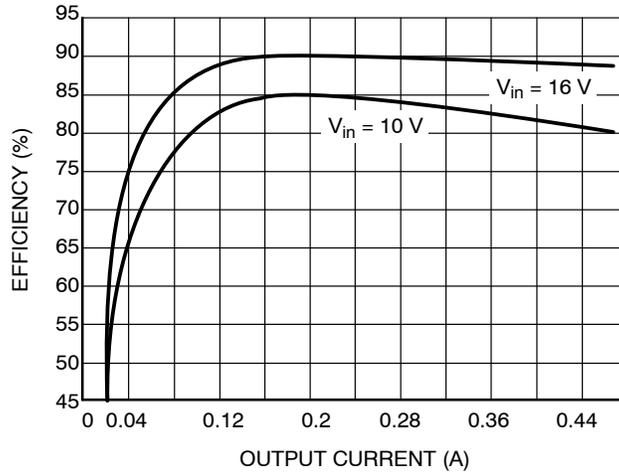


Figure 22. Boost Demoboard Photo

# NCP3064, NCP3064B, NCV3064

**Table 6. TEST RESULTS**

|                 |  |                      |
|-----------------|--|----------------------|
| Line Regulation | $V_{in} = 9\text{ V to }15\text{ V}, V_{out} = 24\text{ V}, I_{out} = 250\text{ mA}$ | 3 mV                 |
| Load Regulation | $V_{in} = 12\text{ V}, V_{out} = 24\text{ V}, I_{out} = 50\text{ to }350\text{ mA}$  | 5 mV                 |
| Output Ripple   | $V_{in} = 12\text{ V}, V_{out} = 24\text{ V}, I_{out} = 50\text{ to }350\text{ mA}$  | < 350 mV Peak - Peak |
| Efficiency      | $V_{in} = 12\text{ V}, V_{out} = 24\text{ V}, I_{out} = 200\text{ mA}$               | 86%                  |



**Figure 23. Efficiency vs. Output Current Current for Boost Demoboard**

# NCP3064, NCP3064B, NCV3064

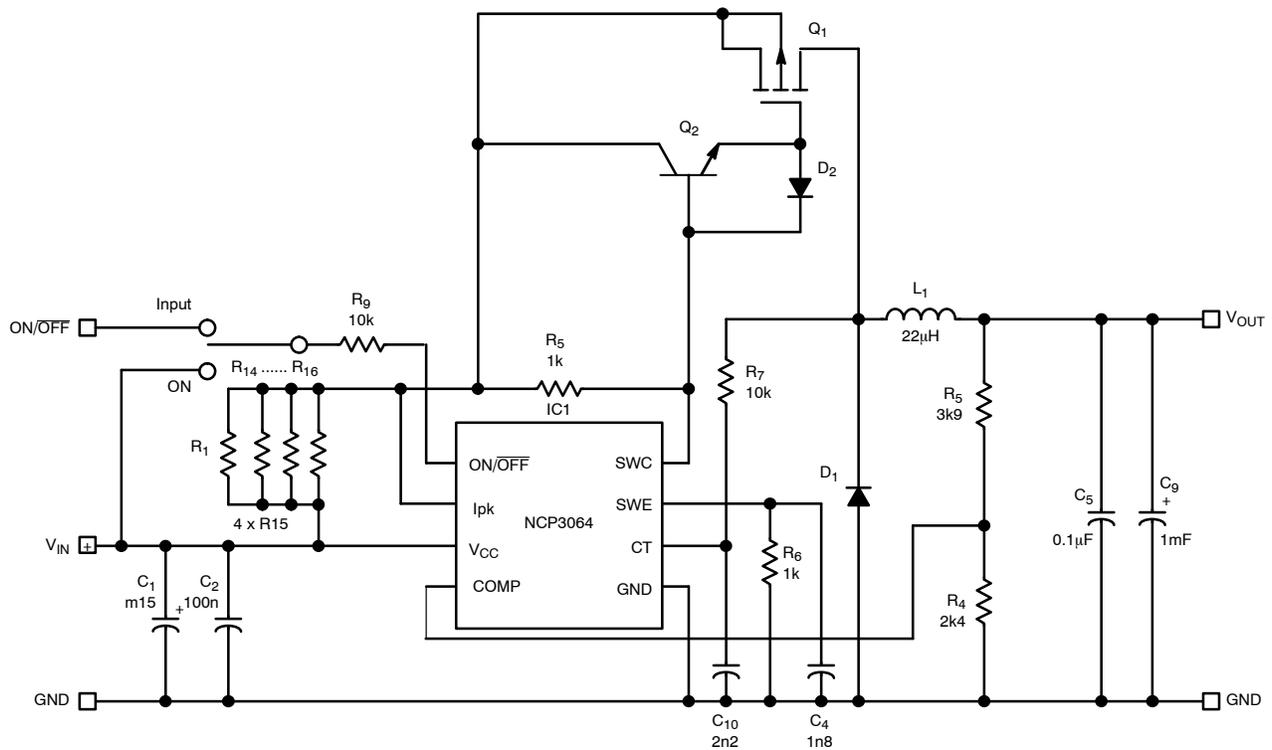


Figure 24. Typical Buck with External Transistor Application Schematic

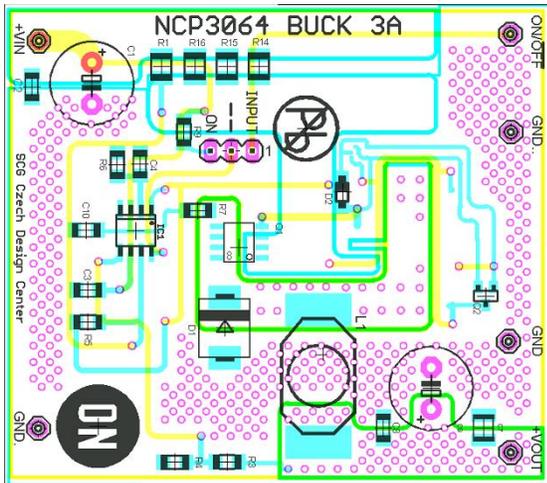
Table 7. TESTED PARAMETERS

| Parameter | Input Voltage (V) | Output Voltage (V) | Input Current (A) | Output Current (A) |
|-----------|-------------------|--------------------|-------------------|--------------------|
| Value     | 10 – 16           | 3.3                | Max. 1.25         | Max. 3             |

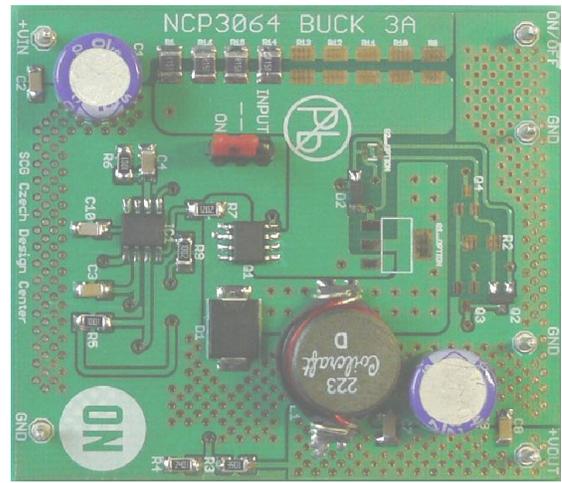
Table 8. BILL OF MATERIAL

| Designator        | Qty | Description         | Value    | Tolerance | Footprint | Manufacturer     | Manufacturer Part Number |
|-------------------|-----|---------------------|----------|-----------|-----------|------------------|--------------------------|
| R1, R14, R15, R16 | 4   | Resistor            | 0.15R    | 1%        | 1206      | Susumu           | RL1632R-R150-F           |
| R5, R6            | 2   | Resistor            | 1k       | 1%        | 1206      | ROHM             | MCR18EZH1001             |
| R3                | 1   | Resistor            | 3k9      | 1%        | 1206      | ROHM             | MCR18EZH3901             |
| R4                | 1   | Resistor            | 2k4      | 1%        | 1206      | ROHM             | MCR18EZH2401             |
| R7;R9             | 2   | Resistor            | 10k      | 1%        | 1206      | ROHM             | MCR18EZH1002             |
| C1                | 1   | Capacitor           | 270µF    | 20%       | 10 x 16   | PANASONIC        | EEUFC1V271               |
| C4                | 1   | Capacitor           | 1n8      | 10%       | 1206      | Kemet            | C1206C182K5RACTU         |
| C2, C8            | 2   | Capacitor           | 100nF    | 10%       | 1206      | Kemet            | C1206C104K5RACTU         |
| C9                | 1   | Capacitor           | 1mF      | 20%       | F8        | SANYO            | 4SA1000M                 |
| C10               | 1   | Capacitor           | 2.2nF    | 10%       | 1206      | Kemet            | C1206C222K5RACTU         |
| Q1                | 1   | Transistor          | MMSF7P03 | -         | SOIC8     | ON Semiconductor | MMSF7P03H2R2G            |
| Q2                | 1   | Transistor NPN      | MMBT489L | -         | SOT-23    | ON Semiconductor | MMBT489LT1G              |
| D2                | 1   | Diode               | MBR130T  | -         | SOD-123   | ON Semiconductor | MBR130T1G                |
| IC1               | 1   | Switching Regulator | NCP3064  | -         | SOIC8     | ON Semiconductor | NCP3064DR2G              |
| D1                | 1   | Diode               | MBRS330T | -         | SMC       | ON Semiconductor | MBRS330T3G               |
| L1                | 1   | Inductor            | 22µH     | 20%       | Coilcraft | Coilcraft        | DO5040H-223MLB           |

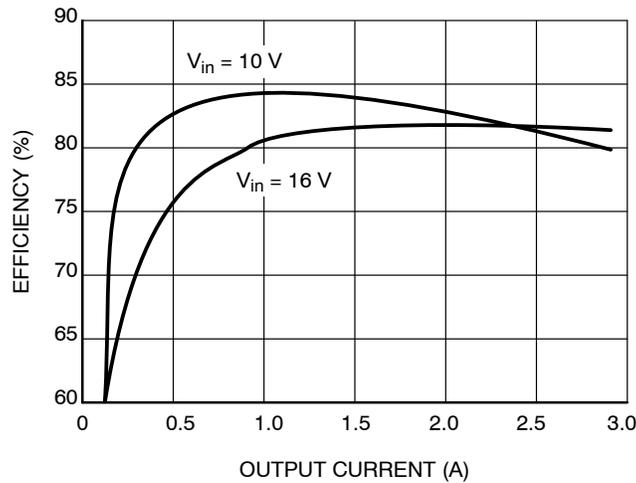
# NCP3064, NCP3064B, NCV3064



**Figure 25. Buck Demoboard with External PMOS Transistor Layout**



**Figure 26. Buck Demoboard with External PMOS Transistor Photo**



**Figure 27. Efficiency vs. Output Current Current for Buck Demoboard with External PMOS Transistor**

**Table 9. TEST RESULTS**

|                 |  |                      |
|-----------------|--|----------------------|
| Line Regulation | $V_{in} = 9\text{ V to }15\text{ V}, V_{out} = 3.3\text{ V}, I_{out} = 2\text{ A}$   | 8 mV                 |
| Load Regulation | $V_{in} = 12\text{ V}, V_{out} = 3.3\text{ V}, I_{out} = 0.5\text{ to }3.0\text{ A}$ | 10 mV                |
| Output Ripple   | $V_{in} = 12\text{ V}, V_{out} = 3.3\text{ V}, I_{out} = 0.5\text{ to }3.0\text{ A}$ | < 300 mV Peak - Peak |
| Efficiency      | $V_{in} = 12\text{ V}, V_{out} = 3.3\text{ V}, I_{out} = 2\text{ A}$                 | 82%                  |

## NCP3064, NCP3064B, NCV3064

The picture in Figure 24. Typical Buck Application Schematic shows typical configuration with external PMOS transistor. Resistor R7 connected between timing capacitor TC Pin and SWE Pin provides a pulse feedback voltage. The pulse feedback approach increases the operating frequency by up to 50%. Figure 28, Oscillator Frequency vs. Timing Capacitor with Pulse Feedback, shows the impact to the oscillator frequency at buck converter for  $V_{in} = 12\text{ V}$  and  $V_{out} = 3.3\text{ V}$  with pulse feedback resistor  $R_7 = 10\text{ k}\Omega$ . It also creates more regular switching waveforms with constant operating frequency which results in lower ripple voltage and improved efficiency.

If the application allows  $\overline{\text{ON/OFF}}$  pin to be biased by voltage and the power supply is not connected to  $V_{CC}$  pin at the same time, then it is recommended to limit  $\overline{\text{ON/OFF}}$  current by resistor with value  $10\text{ k}\Omega$  to protect the NCP3064 device. This situation is mentioned in Figure 29,  $\overline{\text{ON/OFF}}$  Serial Resistor Connection.

This resistor shifts the  $\overline{\text{ON/OFF}}$  threshold by about  $200\text{ mV}$  to higher value, but the TTL logic compatibility is kept in full range of input voltage and operating temperature range.

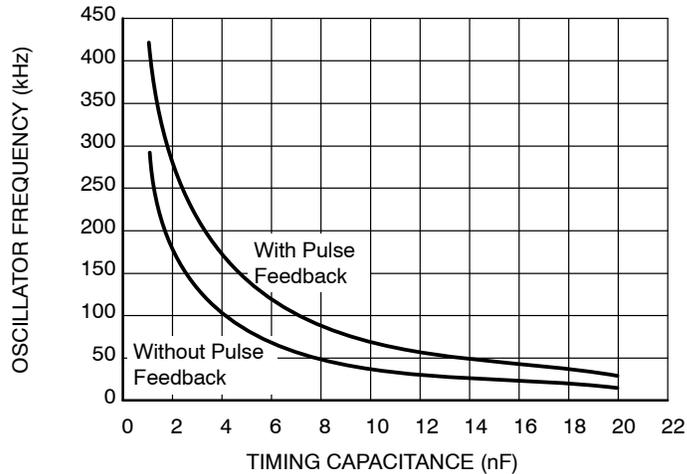


Figure 28. Oscillator Frequency vs. Timing Capacitor with Pulse Feedback

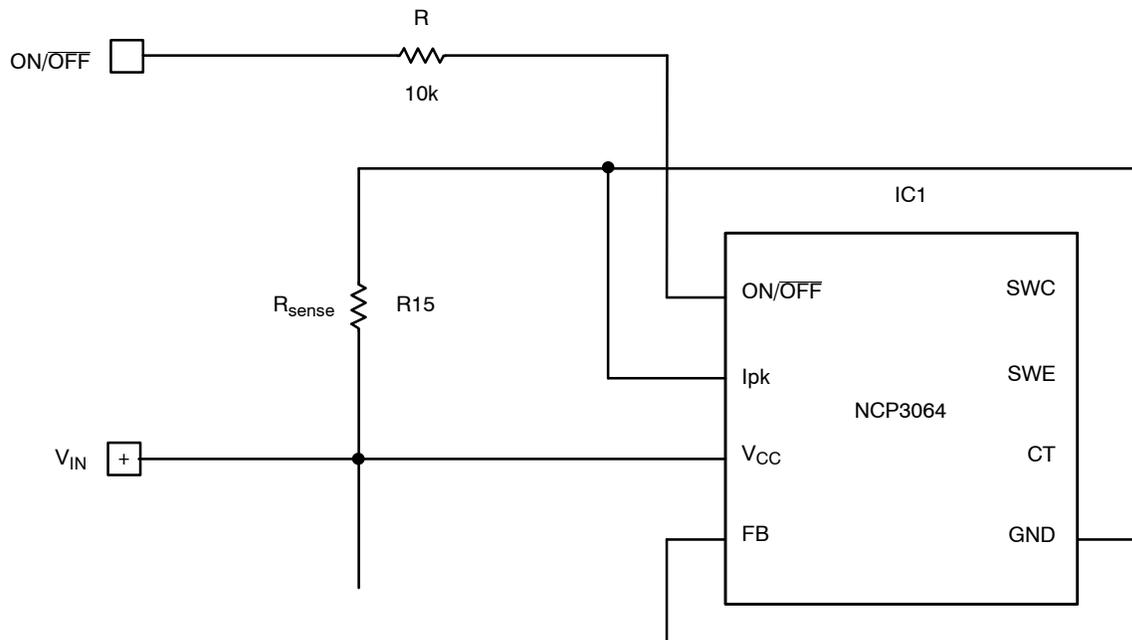


Figure 29.  $\overline{\text{ON/OFF}}$  Serial Resistor Connection

## NCP3064, NCP3064B, NCV3064

### ORDERING INFORMATION

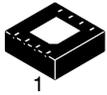
| Device        | Package             | Shipping†                |
|---------------|---------------------|--------------------------|
| NCP3064MNTXG  | DFN-8<br>(Pb-Free)  | 4000 Units / Tape & Reel |
| NCP3064BMNTXG | DFN-8<br>(Pb-Free)  | 4000 Units / Tape & Reel |
| NCP3064PG     | PDIP-8<br>(Pb-Free) | 50 Units / Rail          |
| NCP3064BPG    | PDIP-8<br>(Pb-Free) | 50 Units / Rail          |
| NCP3064DR2G   | SOIC-8<br>(Pb-Free) | 2500 Units / Tape & Reel |
| NCP3064BDR2G  | SOIC-8<br>(Pb-Free) | 2500 Units / Tape & Reel |
| NCV3064MNTXG  | DFN-8<br>(Pb-Free)  | 4000 Units / Tape & Reel |
| NCV3064PG     | PDIP-8<br>(Pb-Free) | 50 Units / Rail          |
| NCV3064DR2G   | SOIC-8<br>(Pb-Free) | 2500 Units / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

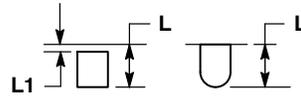
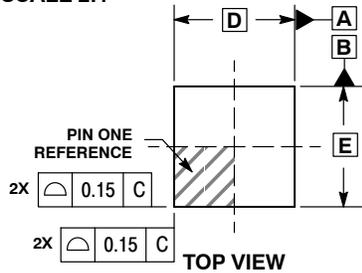
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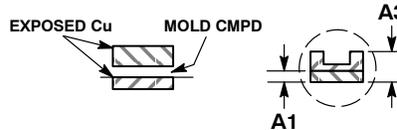
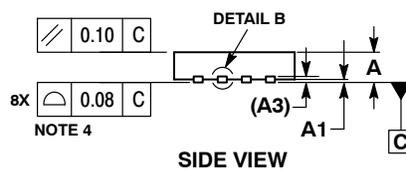
SCALE 2:1

### DFN8, 4x4 CASE 488AF-01 ISSUE C

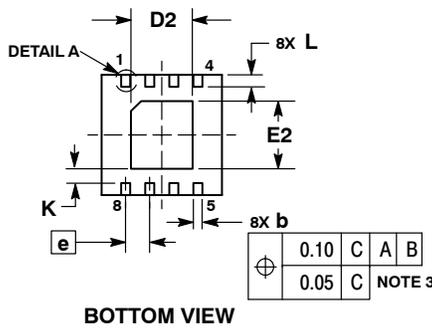
DATE 15 JAN 2009



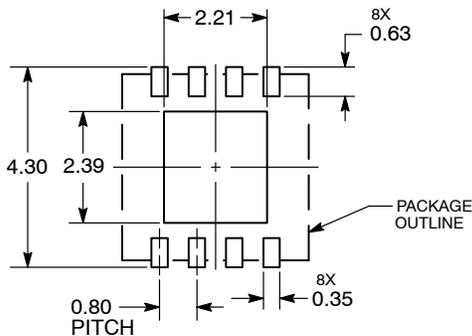
DETAIL A  
OPTIONAL  
CONSTRUCTIONS



DETAIL B  
ALTERNATE  
CONSTRUCTIONS



### SOLDERING FOOTPRINT\*



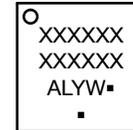
DIMENSIONS: MILLIMETERS

NOTES:

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DETAILS A AND B SHOW OPTIONAL CONSTRUCTIONS FOR TERMINALS.

| MILLIMETERS |      |      |
|-------------|------|------|
| DIM         | MIN  | MAX  |
| A           | 0.80 | 1.00 |
| A1          | 0.00 | 0.05 |
| A3          | 0.20 | REF  |
| b           | 0.25 | 0.35 |
| D           | 4.00 | BSC  |
| D2          | 1.91 | 2.21 |
| E           | 4.00 | BSC  |
| E2          | 2.09 | 2.39 |
| e           | 0.80 | BSC  |
| K           | 0.20 | ---  |
| L           | 0.30 | 0.50 |
| L1          | ---  | 0.15 |

### GENERIC MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

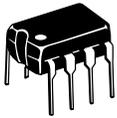
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

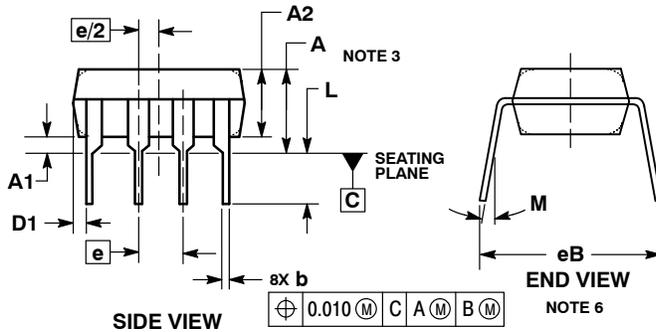
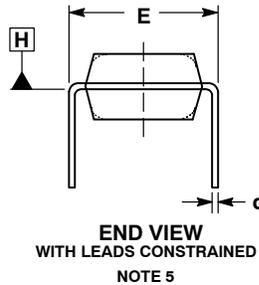
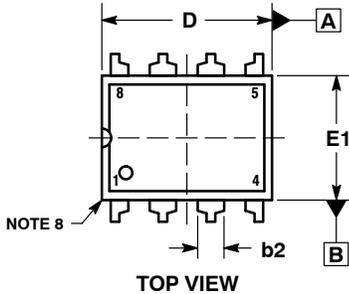
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SCALE 1:1

PDIP-8  
CASE 626-05  
ISSUE P

DATE 22 APR 2015

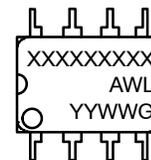


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | ----      | 0.210 | ----        | 5.33  |
| A1  | 0.015     | ----  | 0.38        | ----  |
| A2  | 0.115     | 0.195 | 2.92        | 4.95  |
| b   | 0.014     | 0.022 | 0.35        | 0.56  |
| b2  | 0.060 TYP |       | 1.52 TYP    |       |
| C   | 0.008     | 0.014 | 0.20        | 0.36  |
| D   | 0.355     | 0.400 | 9.02        | 10.16 |
| D1  | 0.005     | ----  | 0.13        | ----  |
| E   | 0.300     | 0.325 | 7.62        | 8.26  |
| E1  | 0.240     | 0.280 | 6.10        | 7.11  |
| e   | 0.100 BSC |       | 2.54 BSC    |       |
| eB  | ----      | 0.430 | ----        | 10.92 |
| L   | 0.115     | 0.150 | 2.92        | 3.81  |
| M   | ----      | 10°   | ----        | 10°   |

GENERIC  
MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- STYLE 1:  
PIN 1. AC IN  
2. DC + IN  
3. DC - IN  
4. AC IN  
5. GROUND  
6. OUTPUT  
7. AUXILIARY  
8. V<sub>CC</sub>

|                  |             |  |
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

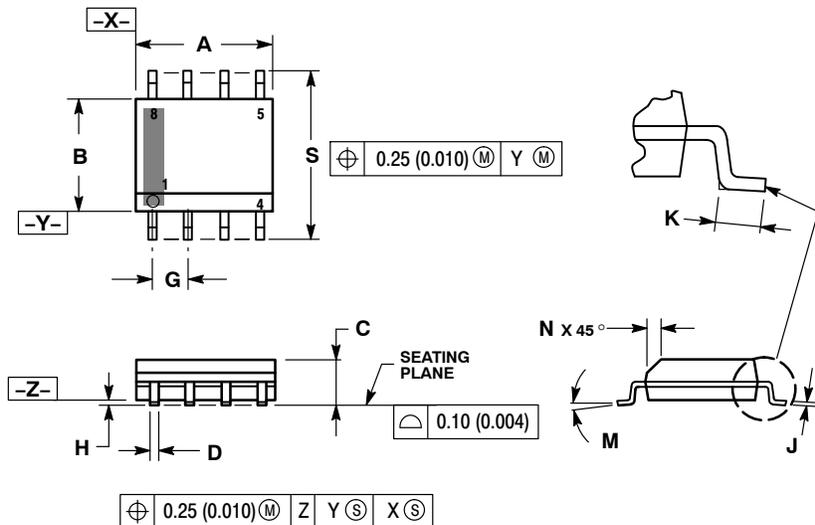
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SCALE 1:1

SOIC-8 NB  
CASE 751-07  
ISSUE AK

DATE 16 FEB 2011



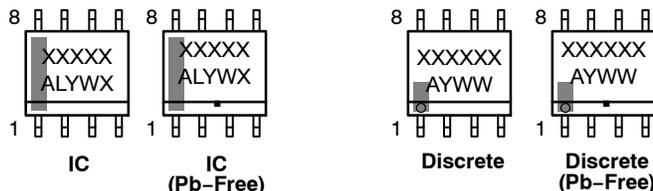
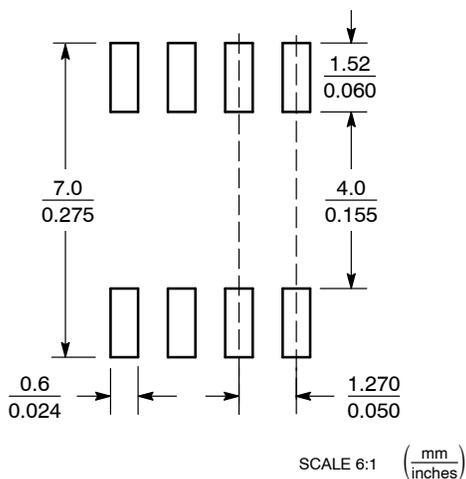
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS |      | INCHES    |       |
|-----|-------------|------|-----------|-------|
|     | MIN         | MAX  | MIN       | MAX   |
| A   | 4.80        | 5.00 | 0.189     | 0.197 |
| B   | 3.80        | 4.00 | 0.150     | 0.157 |
| C   | 1.35        | 1.75 | 0.053     | 0.069 |
| D   | 0.33        | 0.51 | 0.013     | 0.020 |
| G   | 1.27 BSC    |      | 0.050 BSC |       |
| H   | 0.10        | 0.25 | 0.004     | 0.010 |
| J   | 0.19        | 0.25 | 0.007     | 0.010 |
| K   | 0.40        | 1.27 | 0.016     | 0.050 |
| M   | 0°          | 8°   | 0°        | 8°    |
| N   | 0.25        | 0.50 | 0.010     | 0.020 |
| S   | 5.80        | 6.20 | 0.228     | 0.244 |

### GENERIC MARKING DIAGRAM\*

### SOLDERING FOOTPRINT\*



XXXXXX = Specific Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
■ = Pb-Free Package

XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

|                  |             |  |
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**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

- |  |   |   |   |
|--|---|---|---|
| <p><b>STYLE 1:</b><br/> PIN 1. EMITTER<br/> 2. COLLECTOR<br/> 3. COLLECTOR<br/> 4. EMITTER<br/> 5. EMITTER<br/> 6. BASE<br/> 7. BASE<br/> 8. EMITTER</p>   | <p><b>STYLE 2:</b><br/> PIN 1. COLLECTOR, DIE, #1<br/> 2. COLLECTOR, #1<br/> 3. COLLECTOR, #2<br/> 4. COLLECTOR, #2<br/> 5. BASE, #2<br/> 6. EMITTER, #2<br/> 7. BASE, #1<br/> 8. EMITTER, #1</p>               | <p><b>STYLE 3:</b><br/> PIN 1. DRAIN, DIE #1<br/> 2. DRAIN, #1<br/> 3. DRAIN, #2<br/> 4. DRAIN, #2<br/> 5. GATE, #2<br/> 6. SOURCE, #2<br/> 7. GATE, #1<br/> 8. SOURCE, #1</p>                            | <p><b>STYLE 4:</b><br/> PIN 1. ANODE<br/> 2. ANODE<br/> 3. ANODE<br/> 4. ANODE<br/> 5. ANODE<br/> 6. ANODE<br/> 7. ANODE<br/> 8. COMMON CATHODE</p>   |
| <p><b>STYLE 5:</b><br/> PIN 1. DRAIN<br/> 2. DRAIN<br/> 3. DRAIN<br/> 4. DRAIN<br/> 5. GATE<br/> 6. GATE<br/> 7. SOURCE<br/> 8. SOURCE</p>   | <p><b>STYLE 6:</b><br/> PIN 1. SOURCE<br/> 2. DRAIN<br/> 3. DRAIN<br/> 4. SOURCE<br/> 5. SOURCE<br/> 6. GATE<br/> 7. GATE<br/> 8. SOURCE</p>  | <p><b>STYLE 7:</b><br/> PIN 1. INPUT<br/> 2. EXTERNAL BYPASS<br/> 3. THIRD STAGE SOURCE<br/> 4. GROUND<br/> 5. DRAIN<br/> 6. GATE 3<br/> 7. SECOND STAGE Vd<br/> 8. FIRST STAGE Vd</p>                    | <p><b>STYLE 8:</b><br/> PIN 1. COLLECTOR, DIE #1<br/> 2. BASE, #1<br/> 3. BASE, #2<br/> 4. COLLECTOR, #2<br/> 5. COLLECTOR, #2<br/> 6. EMITTER, #2<br/> 7. EMITTER, #1<br/> 8. COLLECTOR, #1</p>                              |
| <p><b>STYLE 9:</b><br/> PIN 1. EMITTER, COMMON<br/> 2. COLLECTOR, DIE #1<br/> 3. COLLECTOR, DIE #2<br/> 4. EMITTER, COMMON<br/> 5. EMITTER, COMMON<br/> 6. BASE, DIE #2<br/> 7. BASE, DIE #1<br/> 8. EMITTER, COMMON</p> | <p><b>STYLE 10:</b><br/> PIN 1. GROUND<br/> 2. BIAS 1<br/> 3. OUTPUT<br/> 4. GROUND<br/> 5. GROUND<br/> 6. BIAS 2<br/> 7. INPUT<br/> 8. GROUND</p>  | <p><b>STYLE 11:</b><br/> PIN 1. SOURCE 1<br/> 2. GATE 1<br/> 3. SOURCE 2<br/> 4. GATE 2<br/> 5. DRAIN 2<br/> 6. DRAIN 2<br/> 7. DRAIN 1<br/> 8. DRAIN 1</p>   | <p><b>STYLE 12:</b><br/> PIN 1. SOURCE<br/> 2. SOURCE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>   |
| <p><b>STYLE 13:</b><br/> PIN 1. N.C.<br/> 2. SOURCE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>  | <p><b>STYLE 14:</b><br/> PIN 1. N-SOURCE<br/> 2. N-GATE<br/> 3. P-SOURCE<br/> 4. P-GATE<br/> 5. P-DRAIN<br/> 6. P-DRAIN<br/> 7. N-DRAIN<br/> 8. N-DRAIN</p>   | <p><b>STYLE 15:</b><br/> PIN 1. ANODE 1<br/> 2. ANODE 1<br/> 3. ANODE 1<br/> 4. ANODE 1<br/> 5. CATHODE, COMMON<br/> 6. CATHODE, COMMON<br/> 7. CATHODE, COMMON<br/> 8. CATHODE, COMMON</p>               | <p><b>STYLE 16:</b><br/> PIN 1. EMITTER, DIE #1<br/> 2. BASE, DIE #1<br/> 3. EMITTER, DIE #2<br/> 4. BASE, DIE #2<br/> 5. COLLECTOR, DIE #2<br/> 6. COLLECTOR, DIE #2<br/> 7. COLLECTOR, DIE #1<br/> 8. COLLECTOR, DIE #1</p> |
| <p><b>STYLE 17:</b><br/> PIN 1. VCC<br/> 2. V2OUT<br/> 3. V1OUT<br/> 4. TXE<br/> 5. RXE<br/> 6. VEE<br/> 7. GND<br/> 8. ACC</p>  | <p><b>STYLE 18:</b><br/> PIN 1. ANODE<br/> 2. ANODE<br/> 3. SOURCE<br/> 4. GATE<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. CATHODE<br/> 8. CATHODE</p>   | <p><b>STYLE 19:</b><br/> PIN 1. SOURCE 1<br/> 2. GATE 1<br/> 3. SOURCE 2<br/> 4. GATE 2<br/> 5. DRAIN 2<br/> 6. MIRROR 2<br/> 7. DRAIN 1<br/> 8. MIRROR 1</p>   | <p><b>STYLE 20:</b><br/> PIN 1. SOURCE (N)<br/> 2. GATE (N)<br/> 3. SOURCE (P)<br/> 4. GATE (P)<br/> 5. DRAIN<br/> 6. DRAIN<br/> 7. DRAIN<br/> 8. DRAIN</p>   |
| <p><b>STYLE 21:</b><br/> PIN 1. CATHODE 1<br/> 2. CATHODE 2<br/> 3. CATHODE 3<br/> 4. CATHODE 4<br/> 5. CATHODE 5<br/> 6. COMMON ANODE<br/> 7. COMMON ANODE<br/> 8. CATHODE 6</p>  | <p><b>STYLE 22:</b><br/> PIN 1. I/O LINE 1<br/> 2. COMMON CATHODE/VCC<br/> 3. COMMON CATHODE/VCC<br/> 4. I/O LINE 3<br/> 5. COMMON ANODE/GND<br/> 6. I/O LINE 4<br/> 7. I/O LINE 5<br/> 8. COMMON ANODE/GND</p> | <p><b>STYLE 23:</b><br/> PIN 1. LINE 1 IN<br/> 2. COMMON ANODE/GND<br/> 3. COMMON ANODE/GND<br/> 4. LINE 2 IN<br/> 5. LINE 2 OUT<br/> 6. COMMON ANODE/GND<br/> 7. COMMON ANODE/GND<br/> 8. LINE 1 OUT</p> | <p><b>STYLE 24:</b><br/> PIN 1. BASE<br/> 2. EMITTER<br/> 3. COLLECTOR/ANODE<br/> 4. COLLECTOR/ANODE<br/> 5. CATHODE<br/> 6. CATHODE<br/> 7. COLLECTOR/ANODE<br/> 8. COLLECTOR/ANODE</p>                                      |
| <p><b>STYLE 25:</b><br/> PIN 1. VIN<br/> 2. N/C<br/> 3. REXT<br/> 4. GND<br/> 5. IOUT<br/> 6. IOUT<br/> 7. IOUT<br/> 8. IOUT</p>   | <p><b>STYLE 26:</b><br/> PIN 1. GND<br/> 2. dv/dt<br/> 3. ENABLE<br/> 4. ILIMIT<br/> 5. SOURCE<br/> 6. SOURCE<br/> 7. SOURCE<br/> 8. VCC</p>  | <p><b>STYLE 27:</b><br/> PIN 1. ILIMIT<br/> 2. OVLO<br/> 3. UVLO<br/> 4. INPUT+<br/> 5. SOURCE<br/> 6. SOURCE<br/> 7. SOURCE<br/> 8. DRAIN</p>  | <p><b>STYLE 28:</b><br/> PIN 1. SW_TO_GND<br/> 2. DASIC OFF<br/> 3. DASIC_SW_DET<br/> 4. GND<br/> 5. V_MON<br/> 6. VBULK<br/> 7. VBULK<br/> 8. VIN</p>  |
| <p><b>STYLE 29:</b><br/> PIN 1. BASE, DIE #1<br/> 2. EMITTER, #1<br/> 3. BASE, #2<br/> 4. EMITTER, #2<br/> 5. COLLECTOR, #2<br/> 6. COLLECTOR, #2<br/> 7. COLLECTOR, #1<br/> 8. COLLECTOR, #1</p>                        | <p><b>STYLE 30:</b><br/> PIN 1. DRAIN 1<br/> 2. DRAIN 1<br/> 3. GATE 2<br/> 4. SOURCE 2<br/> 5. SOURCE 1/DRAIN 2<br/> 6. SOURCE 1/DRAIN 2<br/> 7. SOURCE 1/DRAIN 2<br/> 8. GATE 1</p>                           |   |   |

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